

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of
Applicants : Rhodes et. al
Serial No. : 09/008,531
Filed : 01/16/98
Title : METHOD OF MAKING A SEMICONDUCTOR DEVICE HAVING
IMPROVED CONTACTS TO A THIN CONDUCTIVE LAYER
Docket No. : MIO 0012 V2
Examiner : EATON
Art Unit : 2823

Assistant Commissioner of Patents
Washington, DC 20231



#141c
T. Young
8-11-00

CERTIFICATE OF MAILING

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Gregory J. Adams

Reg. No. 44,494

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Sir:

RESPONSE

AUG 10 2000

TECHNOLOGY CENTER 2800

This paper is being filed in response to the Office Action mailed July 5, 2000.

Reconsideration of the present application is respectfully requested in light of the
remarks and amendments below.

IN THE CLAIMS

31. (Amended) A process for making a semiconductor device comprising:
 forming a [layer of conductive material] conductive layer having a topography
 that includes a substantially vertical component;
 forming a contact disposed adjacent to and contacting said vertical component;
 and
 forming a structure having an opening therein under said conductive layer and
 filling said opening with said conductive material to form said vertical component.

40. (New) A process for making a semiconductor device comprising:
 forming a conductive layer having a thick region; and
 forming a contact physically in contact with the thick region.

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02 FC:102